

1. General description

Planar passivated four quadrant triac in a SOT223 surface-mountable plastic package. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct interfacing to logic level ICs
- · Direct interfacing to low power gate drivers and microcontrollers
- · Medium blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- AC Fan controller
- General purpose low power phase control
- General purpose low power switching

4. Quick reference data

Table 1. Quick reference data

			,	,		,	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage			-	-	400	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 107 \text{ °C}$; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	0.8	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5		-	-	9	A
		full sine wave; $T_{j(init)}$ = 25 °C; t _p = 16.7 ms		-	-	10	A
Tj	junction temperature			-	-	125	°C
Static characte	eristics						-
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>		-	1	5	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 9</u>		-	2	5	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 9</u>	-	2	5	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 9</u>	-	4	7	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	1	10	mA
V _T	on-state voltage	I _T = 0.85 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.35	1.6	V
Dynamic chara	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 268 V; T _j = 110 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	30	45	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_{\rm D}$ = 400 V; T_j = 50 °C; dI_{com}/dt = 0.3 A/ ms; I_T = 0.84 A; gate open circuit	-	5	-	V/µs

5. Pinning information

Table 2. I	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2-71
2	T2	main terminal 2		G sym051
3	G	gate		Symoor
4	T2	main terminal 2	∐1 ∐2 ∐3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BT1308W-400D	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

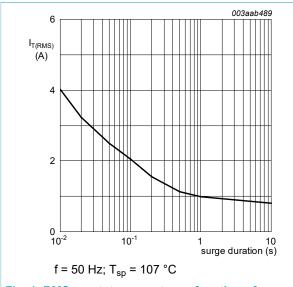


7. Limiting values

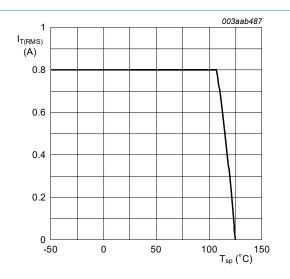
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	400	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 107 °C; <u>Fig. 1; Fig. 2;</u> <u>Fig. 3</u>	-	0.8	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	9	A
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	10	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.32	A²s
dI _T /dt	rate of rise of on-state	I _G = 20 mA; T2+ G+	-	50	A/µs
	current	I _G = 20 mA; T2+ G-	-	50	A/µs
		I _G = 20 mA; T2- G-	-	50	A/µs
		I _G = 20 mA; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	1	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

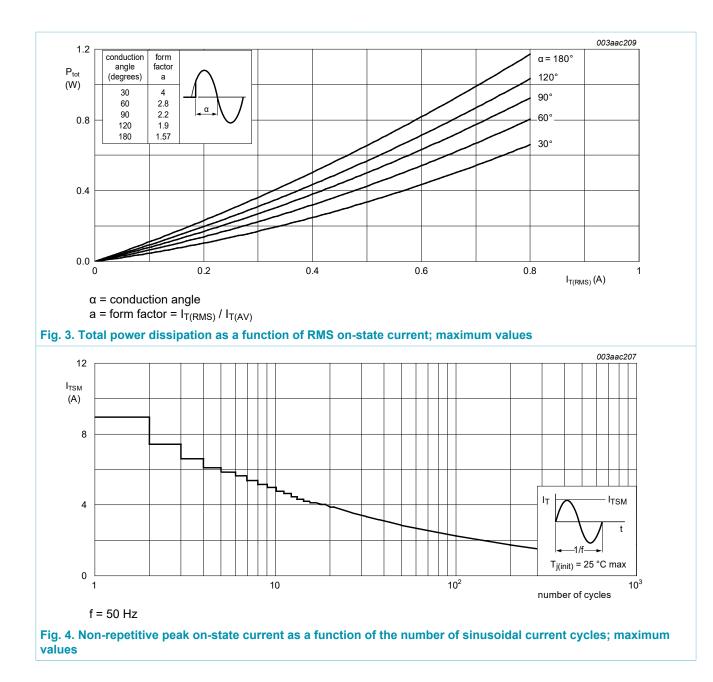






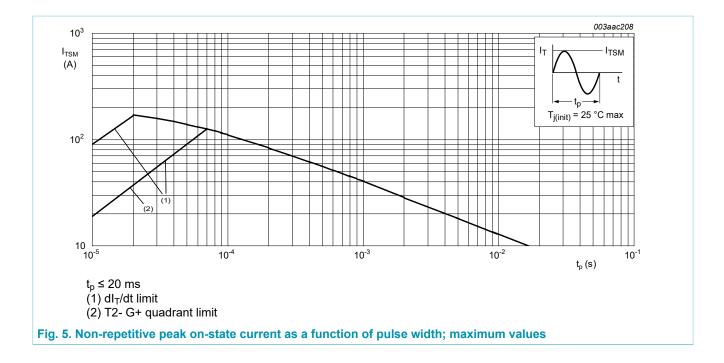


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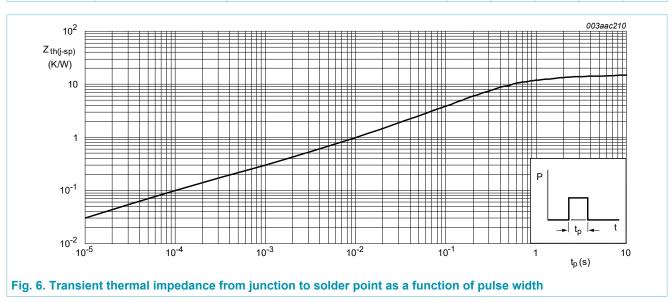
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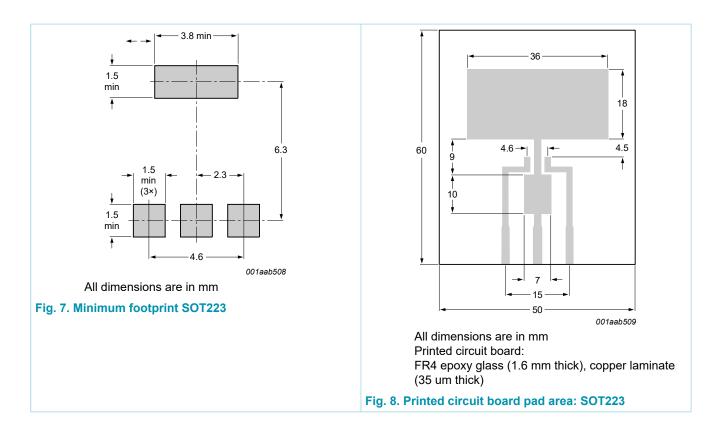
8. Thermal characteristics

Table 5. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full cycle; <u>Fig. 6</u>	-	-	15	K/W
ui(-a)	thermal resistance	full cycle; for minimum footprint; Fig. 7	-	156	-	K/W
	from junction to ambient free air	full cycle; for pad area; <u>Fig. 8</u>	-	70	-	K/W



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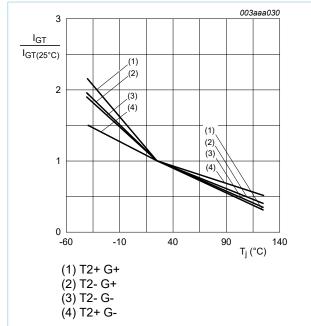


9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>	-	1	5	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 9</u>	-	2	5	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 9</u>	-	2	5	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 9</u>	-	4	7	mA
ΙL	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 10</u>	-	5	10	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 10</u>	-	1	10	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 10</u>	-	1	10	mA
		V _D = 12 V; I _G = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 10</u>	-	2	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	1	10	mA
V _T	on-state voltage	I _T = 0.85 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.35	1.6	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; <u>Fig. 13</u>	-	0.9	1.5	V
		V _D = 400 V; I _T = 0.1 A; T _j = 110 °C; <u>Fig. 13</u>	0.1	0.7	-	V
I _D	off-state current	V _D = 400 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 268 V; T _j = 110 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	30	45	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_{D} = 400 V; T_{j} = 50 °C; dI_{com}/dt = 0.3 A/ ms; I_{T} = 0.84 A; gate open circuit	-	5	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 1 A; V_D = 400 V; I_G = 25 mA; dI_G/dt = 5 A/µs	-	2	-	μs

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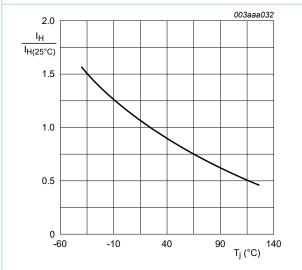
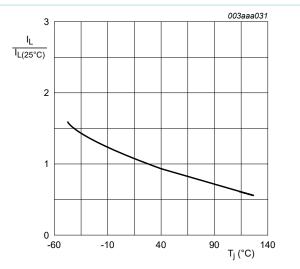
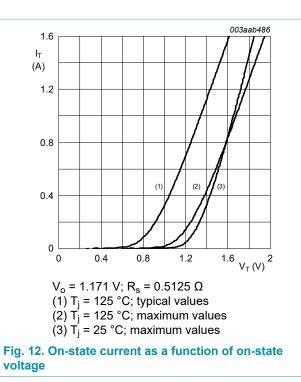


Fig. 11. Normalized holding current as a function of junction temperature

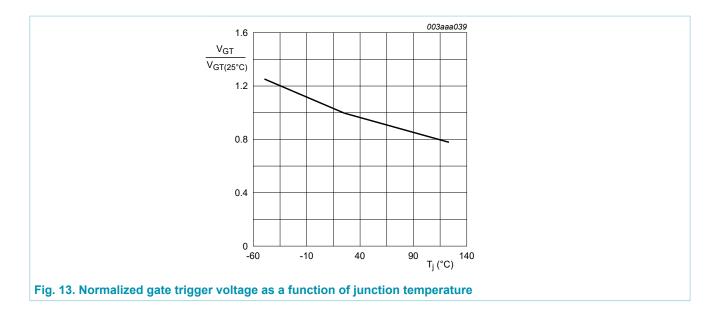






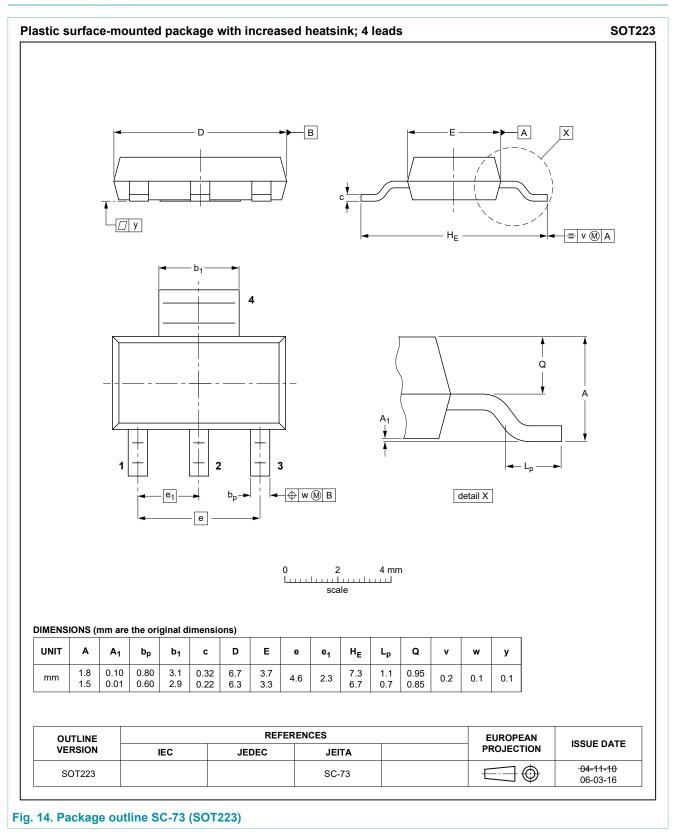
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10. Package outline



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11. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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